N-Channel 100-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- Fast switching speed

Typical	Applica	ations:
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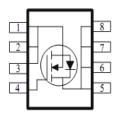
- LED Inverter Circuits
- DC/DC Conversion Circuits
- Motor drives

PRODUCT SUMMARY				
V _{DS} (V)	$V_{DS}(V)$ $r_{DS(on)}(m\Omega)$			
100	48 @ V _{GS} = 10V	8.4		
	55 @ V _{GS} = 5.5V	7.8		









ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter			Limit	Units			
Drain-Source Voltage			100	V			
Gate-Source Voltage	V_{GS}	±20	V				
Continuous Drain Current a	T _A =25°C	l _D	8.4				
Continuous Drain Current	T _A =70°C	'D	6.7	Α			
Pulsed Drain Current ^b	I _{DM}	40					
Continuous Source Current (Diode Conduction) a	I _S	6.4	Α				
Dawer Dissipation a	T _A =25°C	P_{D}	5	W			
Power Dissipation ^a	T _A =70°C			VV			
Operating Junction and Storage Temperature Range			-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter			Maximum	Units			
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	25	°C/W			
Maximum Junction-to-Ambient	Steady State	IΛθJA	65	C/VV			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

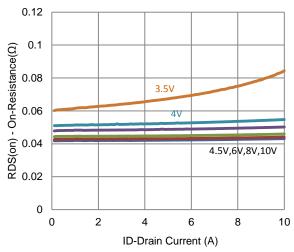
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1 uA		
Zero Gate Voltage Brain Gurrent	I _{DSS}	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$		10 UA		u/\	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	12			Α	
Drain-Source On-Resistance ^a	r	$V_{GS} = 10 \text{ V}, I_{D} = 2 \text{ A}$			48	mΩ	
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = 5.5 \text{ V}, I_D = 1.6 \text{ A}$			55	11122	
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 2 \text{ A}$		8		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = 3.2 \text{ A}, V_{GS} = 0 \text{ V}$		0.75		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 50 \text{ V}, V_{GS} = 5.5 \text{ V},$		16		nC	
Gate-Source Charge	Q_{gs}	$I_{DS} = 30 \text{ V}, \text{ V}_{GS} = 3.3 \text{ V},$ $I_{D} = 2 \text{ A}$		3.8			
Gate-Drain Charge	Q_gd	10 - 2 A		7.3			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 50 \text{ V}, R_{L} = 25 \Omega,$		7			
Rise Time	t _r	$V_{DS} = 50 \text{ V}, R_L - 25 \Omega,$ $I_D = 2 \text{ A},$		8		ne	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		38		ns	
Fall Time	t _f	V GEN = 10 V, 1 (GEN = 0.22		15			
Input Capacitance	C _{iss}			971			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		127		pF	
Reverse Transfer Capacitance	C_{rss}			77			

Notes

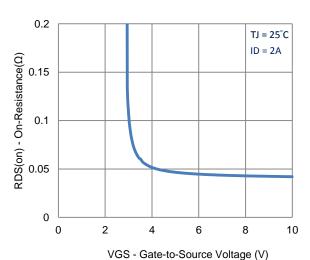
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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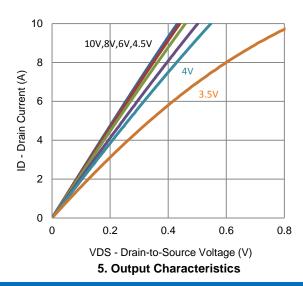
Typical Electrical Characteristics

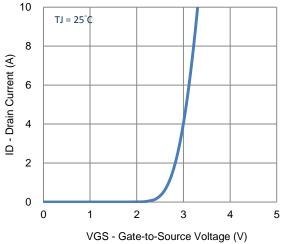


1. On-Resistance vs. Drain Current

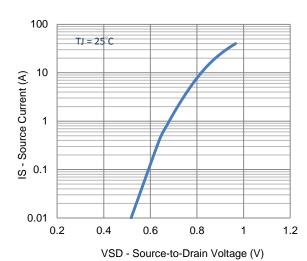


3. On-Resistance vs. Gate-to-Source Voltage

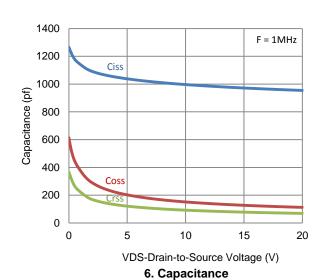




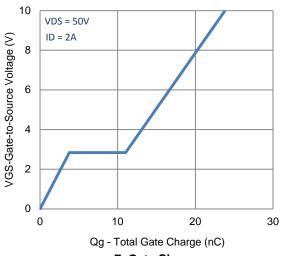
2. Transfer Characteristics



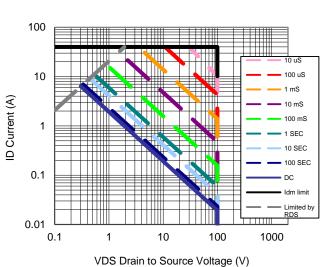
4. Drain-to-Source Forward Voltage



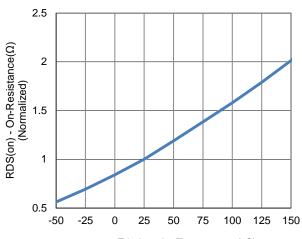
Typical Electrical Characteristics





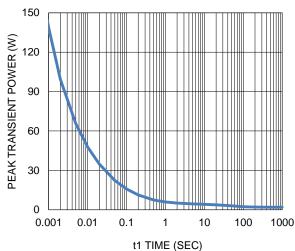


9. Safe Operating Area

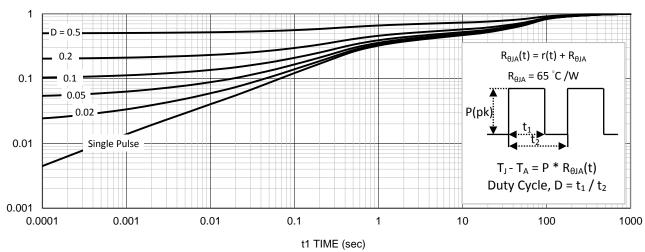


TJ -JunctionTemperature(°C)

8. Normalized On-Resistance Vs Junction Temperature

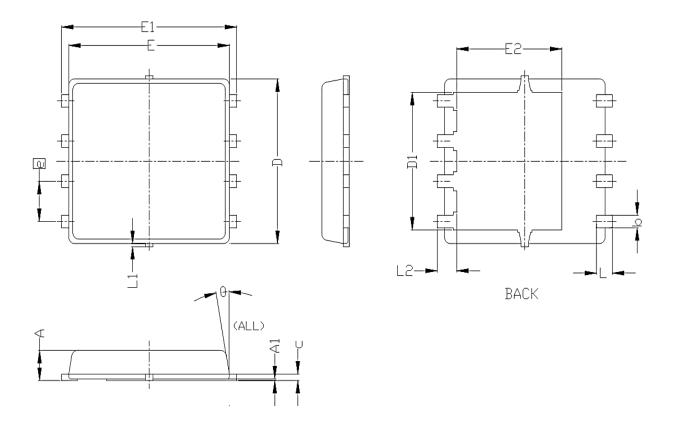


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



CAN MOT C	DIMENSIONS IN MILLIMETERS		DIMENSIONS IN INCHES				
SYMBOLS	MIN	NOM	MAX	MIN	NOM	MAX	
A	0.85	0.95	1.00	0.033	0.037	0.039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
с	0.15	0.20	0.25	0.006	0.008	0.010	
D	5. 20 BSC			0. 205 BSC			
D1	4. 35 BSC			0. 171 BSC			
E		5.55 BSC		0. 219 BSC			
E1	6. 05 BSC			0. 238 BSC			
E2	3. 62 BSC			0. 143 BSC			
e	1. 27 BSC			0. 050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	